

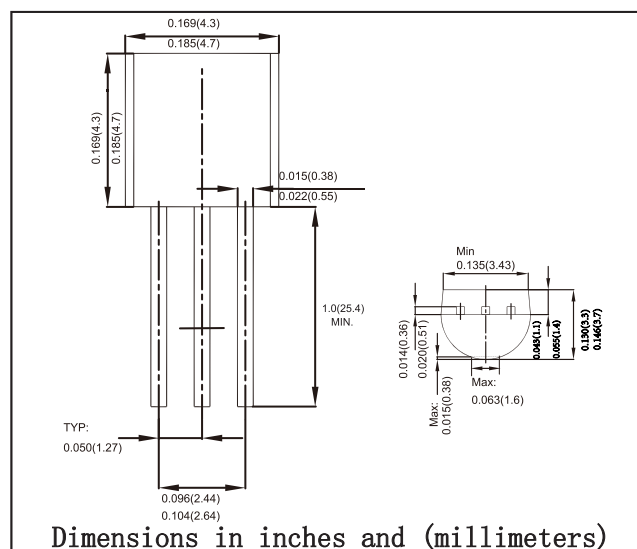
TO-92 Plastic-Encapsulate MOSFETs

Features

- High Total Power Dissipation (PC = 0.45W)
- High hFE and Good Linearity
- Complementary to S9014
- PNP Transistors

MECHANICAL DATA

- Case style:TO-92molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-50	V
V_{CEO}	Collector Emitter Voltage	-45	V
V_{EBO}	Emitter Base Voltage	-5	V
I_c	Collector Current	-0.1	A
P_c	Collector Power Dissipation	450	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (Ta=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1mA, I_B = 0$	-45			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -50V, I_E = 0$			-50	nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V, I_C = 0$			-50	nA
$h_{FE(1)}$	DC current gain	$V_{CE} = -5V, I_C = -1mA$	300		400	
$h_{FE(2)}$		$V_{CE} = -5V, I_C = -10mA$	90			
$h_{FE(3)}$		$V_{CE} = -5V, I_C = -50mA$	50			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-1.0	V
f_T	Transition frequency	$V_{CE}=-5V, I_C=-10mA, f=30MHz$	100			MHz

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

